

General Relationship for the Thermal Oxidation of Silice

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Citation Report

#	ARTICLE	IF	CITATIONS
2	Al precipitate evolution in epitaxial silicon layers induced by thermal oxidation. , 0, , .		1
3	A Literature Survey on Interfaces Thin Dielectric Films and Surfaces - 1965. IEEE Transactions on Parts, Materials and Packaging, 1966, PMP-2, 84-90.	0.3	0
4	Silicon Oxide Films Grown in a Microwave Discharge. Journal of Applied Physics, 1967, 38, 4323-4330.	1.1	86
5	The Influence of Dissolved Oxygen in SiO ₂ on C-V Characteristics. Japanese Journal of Applied Physics, 1967, 6, 1072-1078.	0.8	6
6	A bibliography of metal-insulator-semiconductor studies. IEEE Transactions on Electron Devices, 1967, 14, 728-749.	1.6	37
7	Thermal Oxidation of Silicon: Growth Mechanism and Interface Properties. Physica Status Solidi (B): Basic Research, 1967, 19, 193-202.	0.7	21
8	Another method for the determination of silicon oxide thickness. Solid-State Electronics, 1967, 10, 264-266.	0.8	18
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10	Fowler-Nordheim tunneling in SiO ₂ films. Solid State Communications, 1967, 5, 813-815.	0.9	63
11	Stability and surface charge in the MOS system. International Journal of Electronics, 1968, 24, 1-9.	0.9	16
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19	Section of <i>Biophysics</i> : MASS TRANSPORT THROUGH SILICA AND PHOSPHOSILICATE GLASS FILMS*. Transactions of the New York Academy of Sciences, 1970, 32, 73-84.	0.2	2

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63	Correction to "Electrostatic separation of a charged-particle layer between electrodes". IEEE Transactions on Electron Devices, 1976, 23, 1112-1112.	1.6	0
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